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SELECTIVE DRY ETCH OF A DIELECTRIC FILM

ABSTRACT

A process of etching an oxide layer placed over a nitride layer of a substrate (22) with high selectivity. The process comprises plasma etching the oxide layer of the substrate (22) with a carbon and fluorine-containing gas and with a nitrogen-containing gas. A Si_xN_y species is formed which is deposited on the nitride layer substantially in equilibrium with etching of the nitride layer.

FIG1

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